



Ultrafast THz Pump-Probe experiment in BSTS

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Outline

- Topological Surface state
- Long lifetime of surface carrier in BSTS
- NIR pump-THz probe in BSTS experiment
- MIR pump-THz probe in BSTS experiment
 - Pump-Probe system
 - Experiment data
- Sumarry

Topological surface state

Surface state of topological insulator (TI)

- Linear Dirac dispersion
- Spin-momentum locking

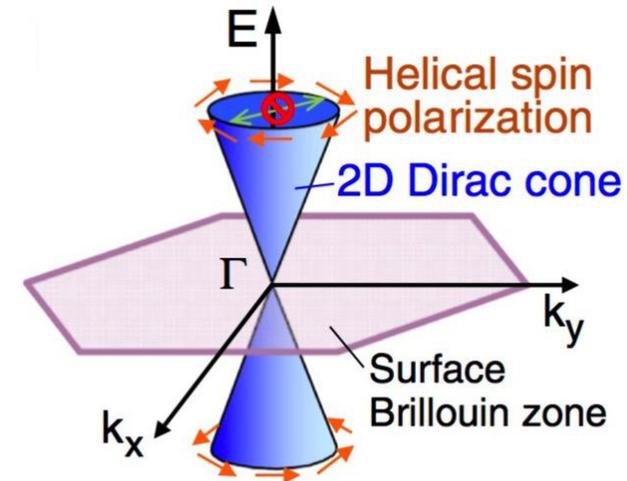
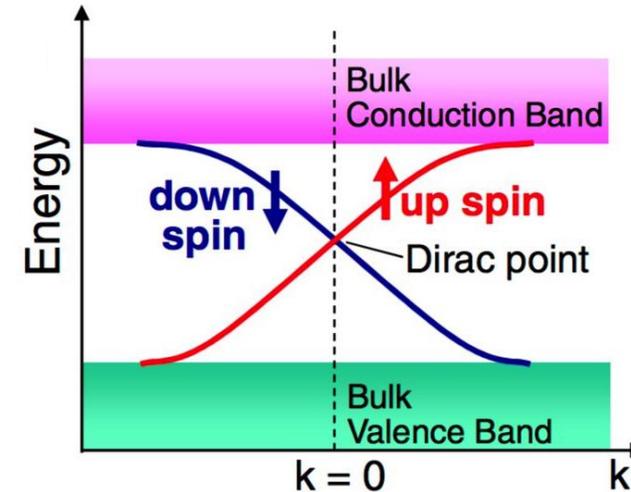
Application

Electronics/spintronics devices

Magneto/Electro-optical device

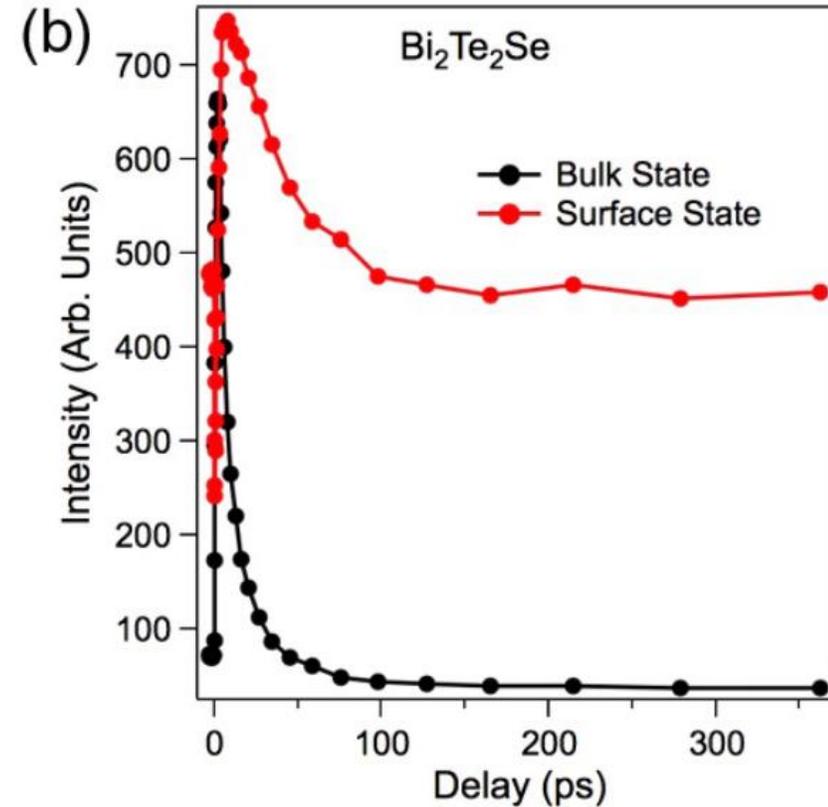
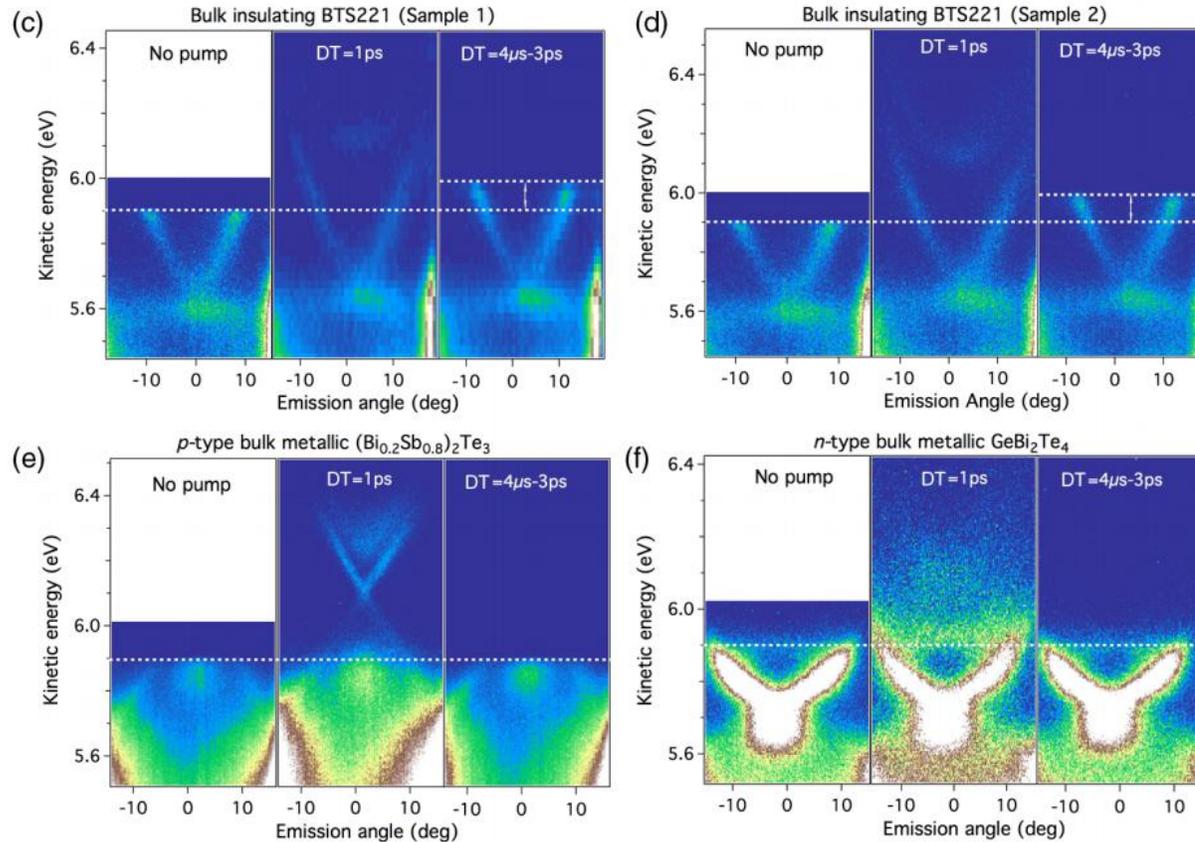
Research interests

- (Ultrafast) Transport property
- Optical control of surface current



Long lifetime of surface carrier

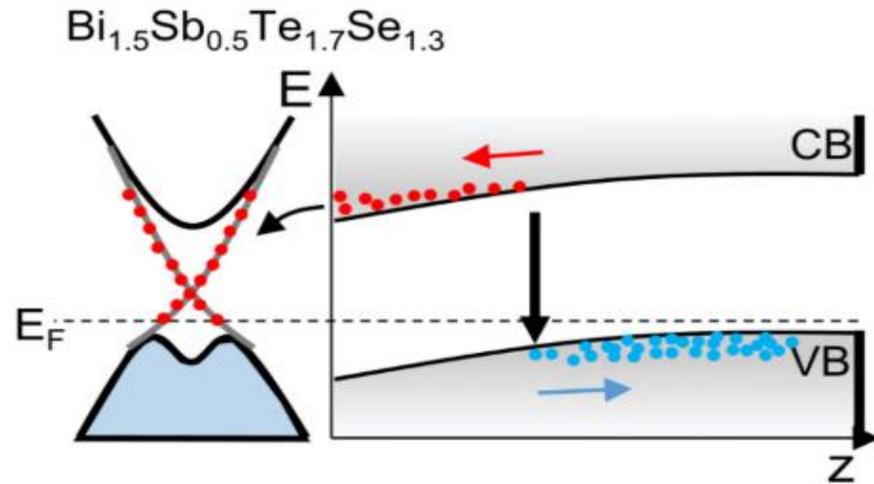
NIR pump- Tr-ARPES for $\text{Bi}_2\text{Te}_2\text{Se}_{[1]}$



After NIR (800 nm) excitation
Bulk carrier diffusion < 100 ps
Slow surface carrier relaxation >> μs

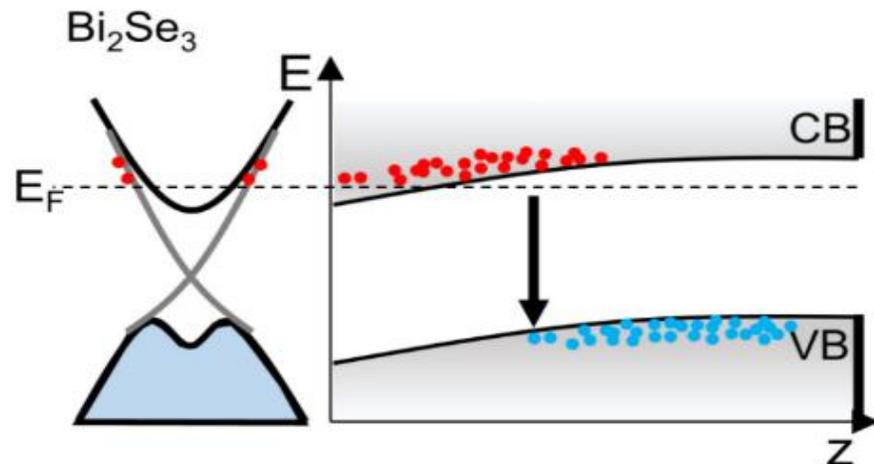
[1] Neupane et al., PRL 115, 116801 (2015)

Long lifetime of surface carrier



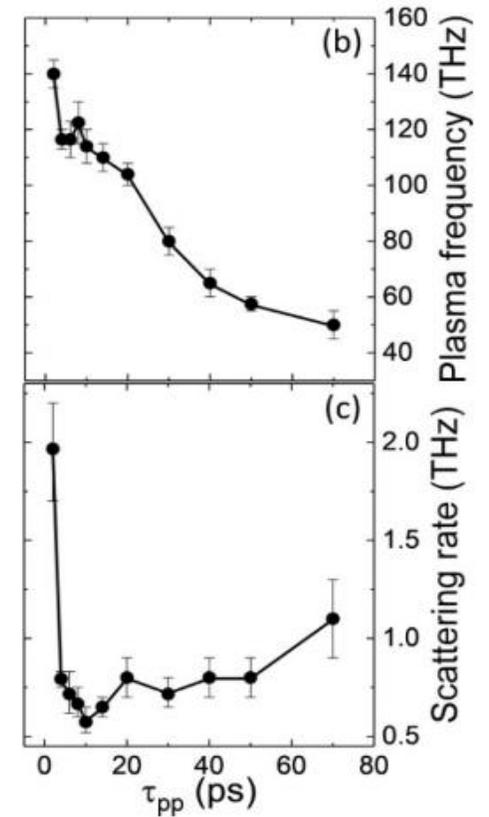
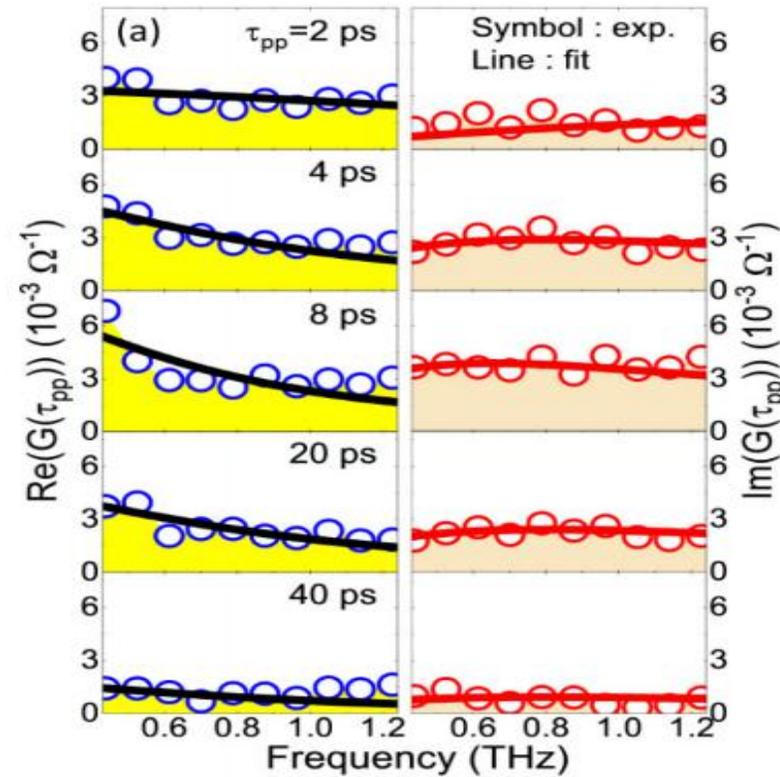
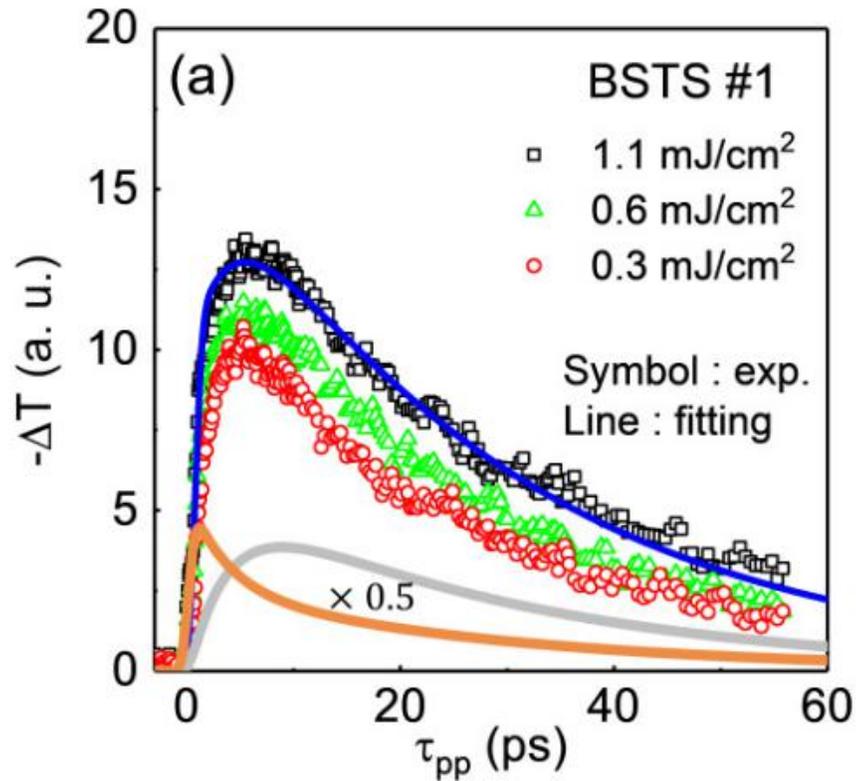
For BSTS, photoexcited electrons and holes are accelerated in the opposite directions.

The confined electrons in the surface state are recombined with bulk holes through the surface-to-bulk transition.



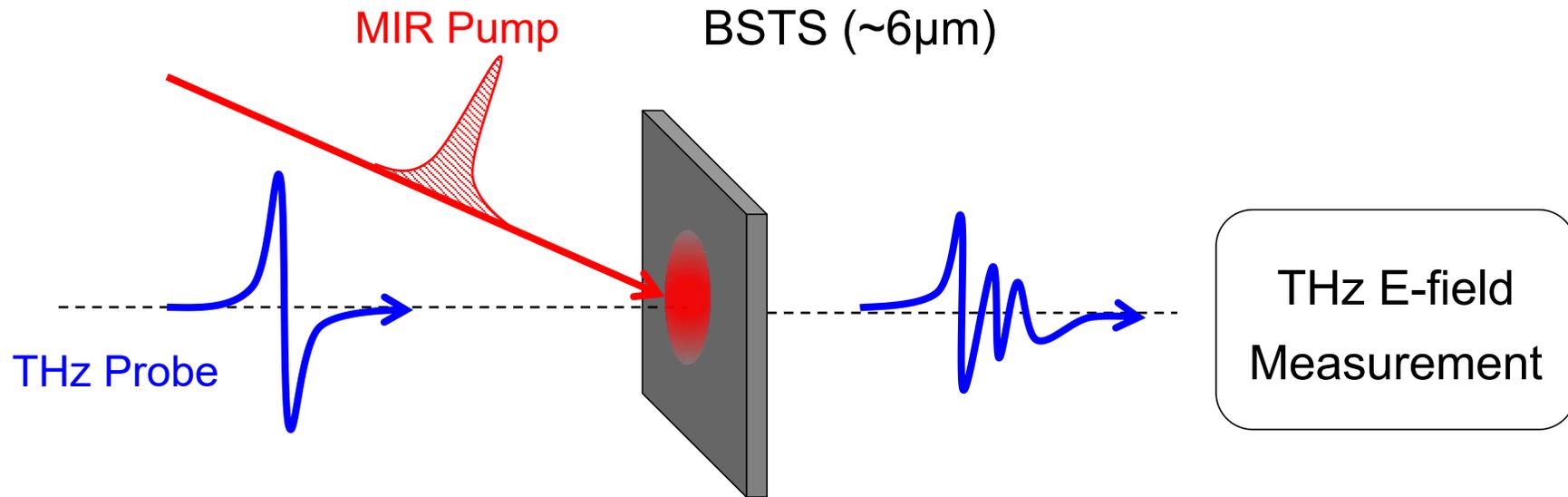
For Bi_2Se_3 , the Fermi level is located crossing the conduction band. The transfer events from the bulk to surface occurs much less than for BSTS.

NIR pump-THz probe in BSTS



After NIR (800 nm) excitation
Bulk carrier diffusion < 60 ps
Slow surface carrier relaxation $\gg \mu\text{s}$

MIR pump-THz probe experiment

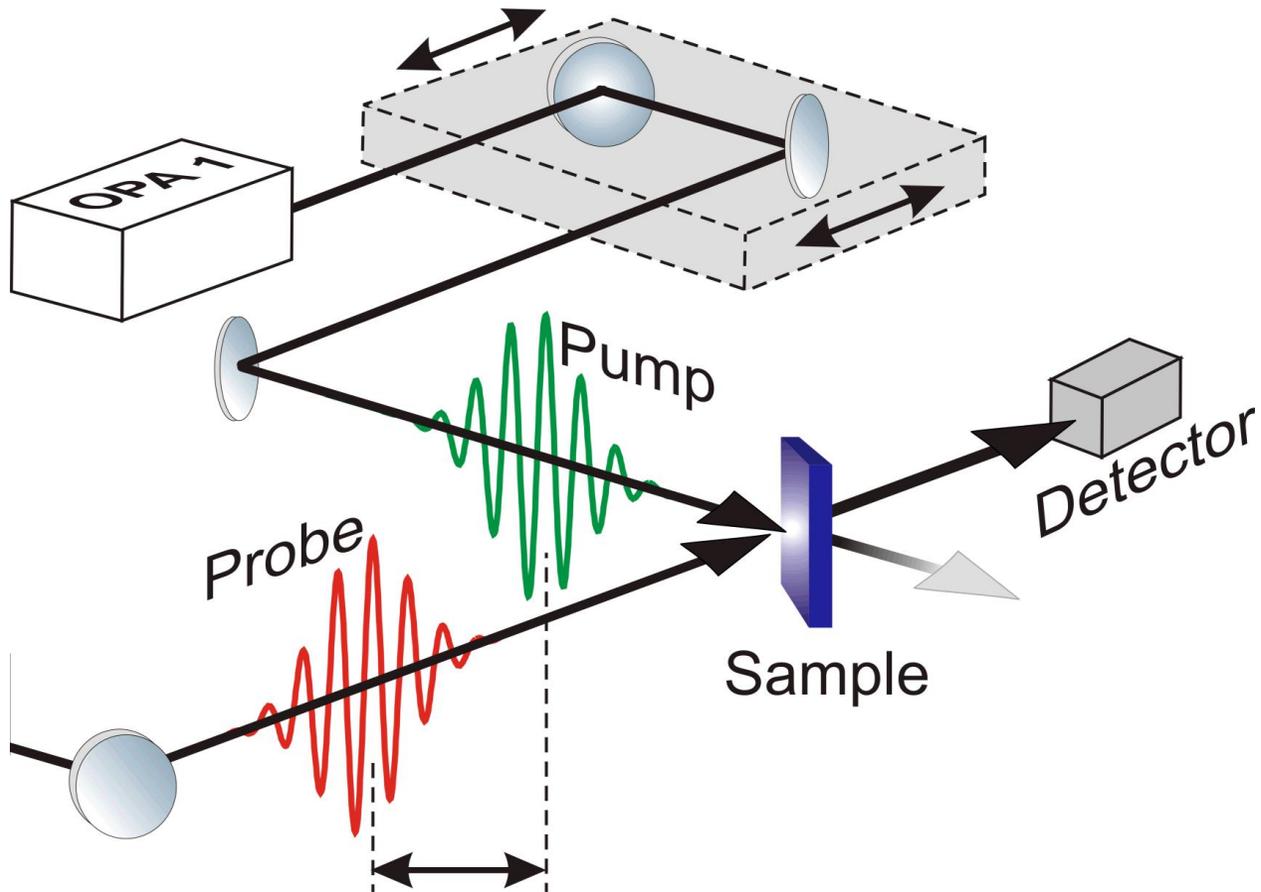


Pump: $\lambda = 8 \mu\text{m}$, ($\sim 0.155 \text{ eV}$) Pulse width $\sim 100\text{fs}$
 $P_{MIR} \sim 8\sim 0.9 \text{ mW}$ Repetition $\sim 1\text{KHz}$
below band gap excitation

Probe: (THz) $0.4 - 7 \text{ THz}$ ($13\text{-}233 \text{ cm}^{-1}$)

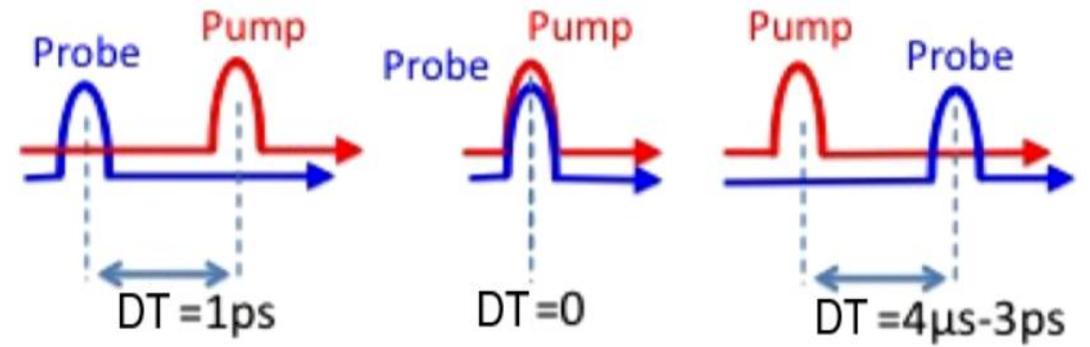
Probe the Drude response of photoexcited carrier

Pump-Probe system



Schematic view of the pump-probe system

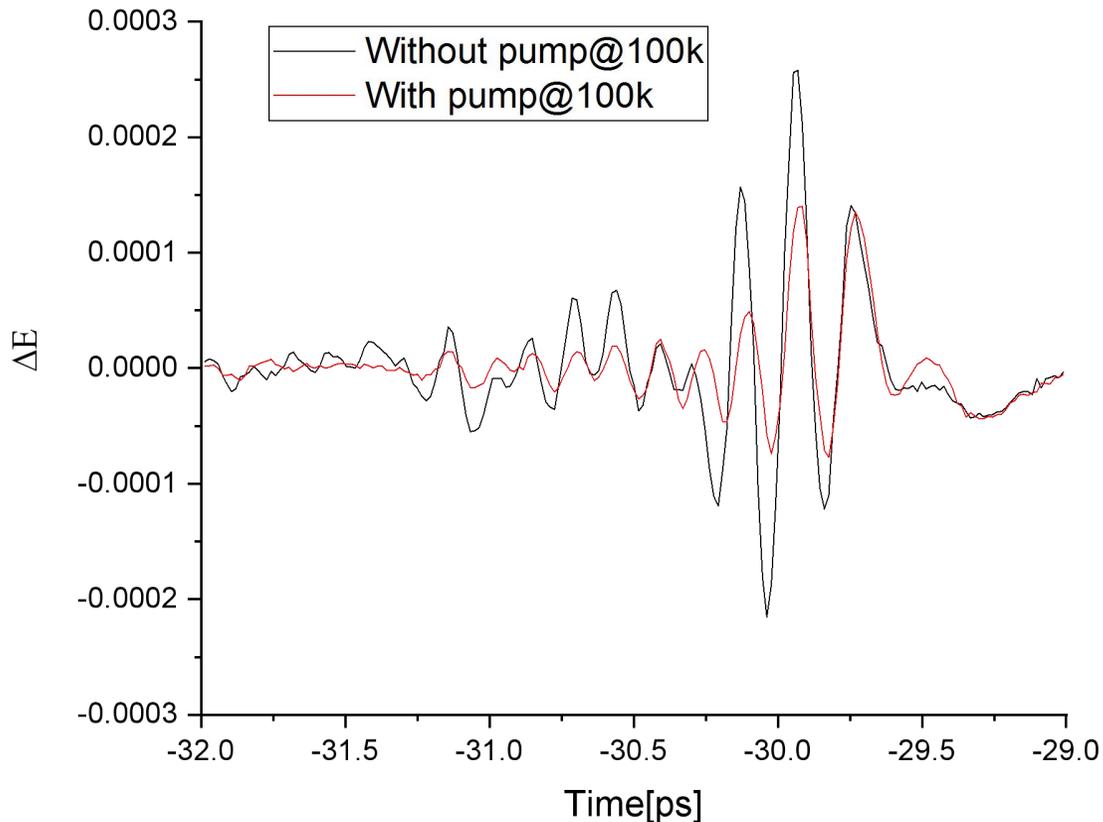
[3] Neupane et al., PRL 115, 116801 (2015)



Delay time between pump and probe beam

By changing the delay time , the optical properties before/after excitation can be measured!

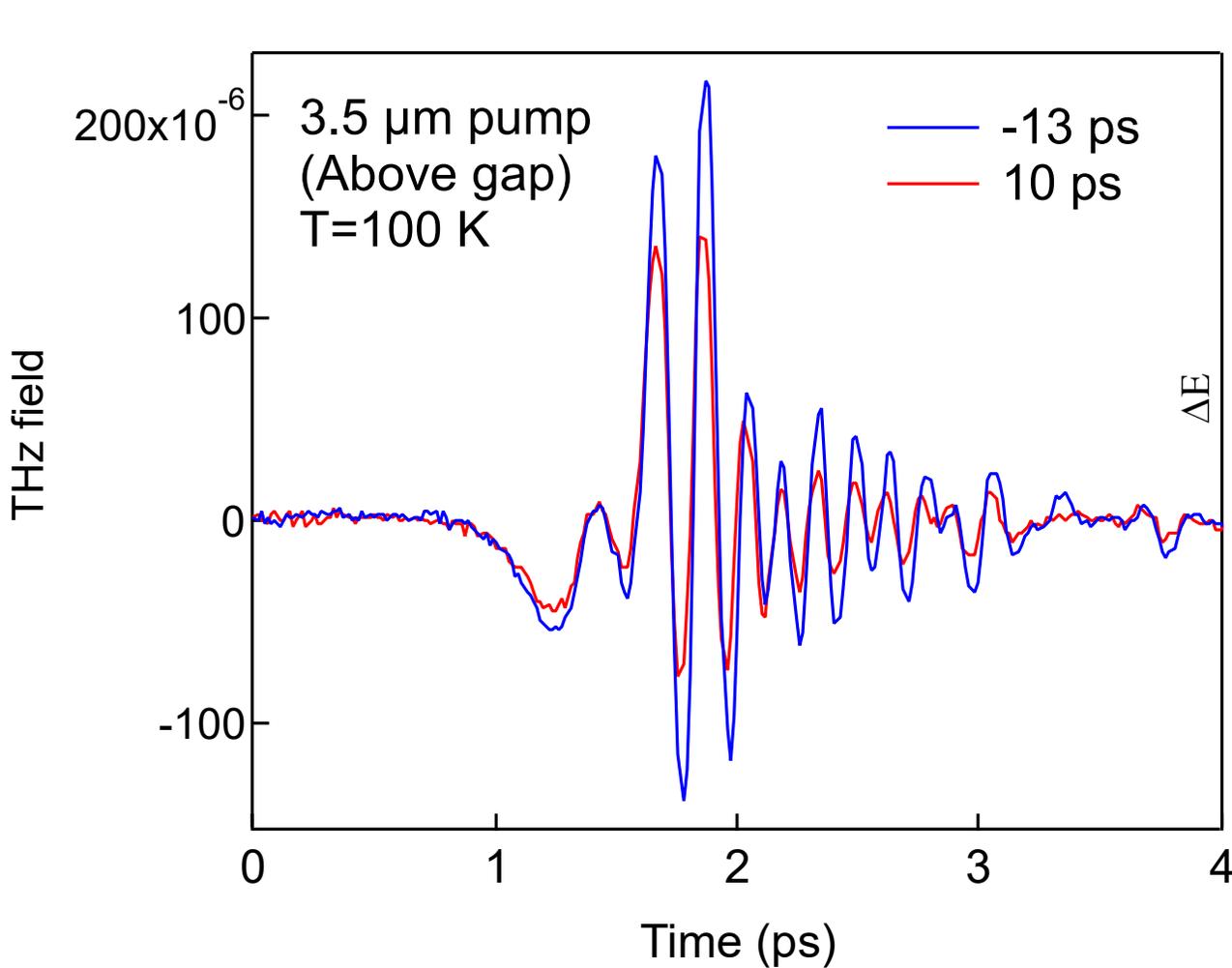
THz spectroscopy with/without pump



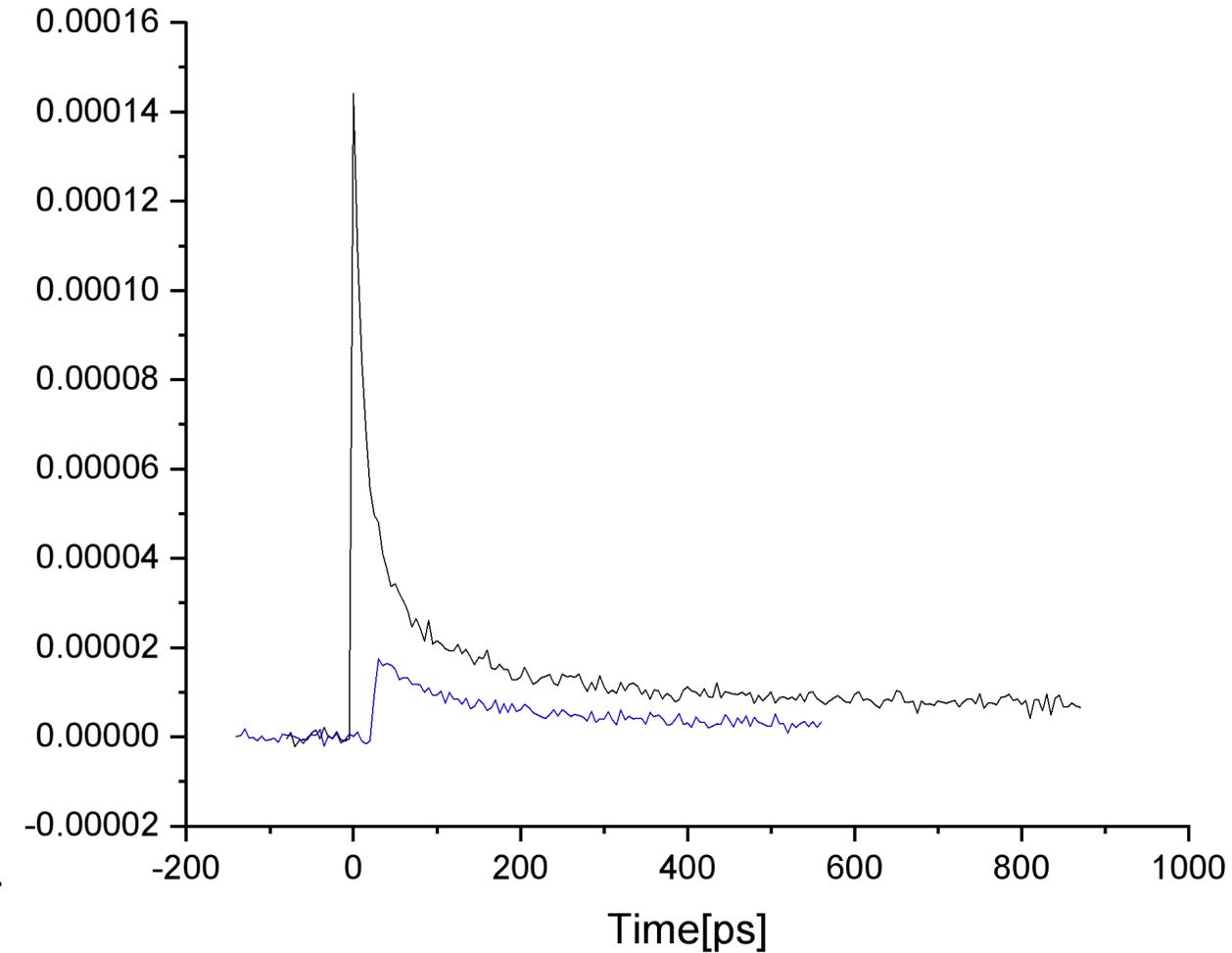
THz spectroscopy with/without pump

- There is an obviously energy change when the pump is open.
- The thermal carrier is activated when the pump is open.

THz peak field change



The THz wave in different position

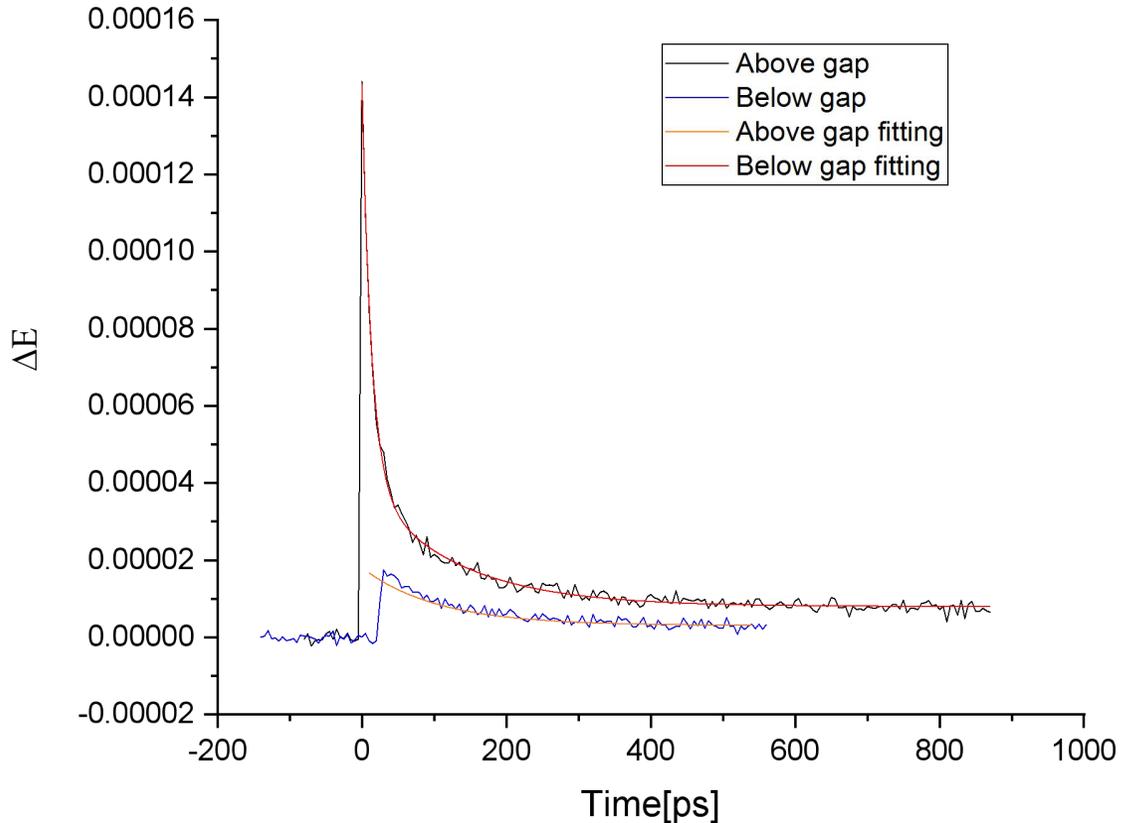


The above/below band gap decay profiles of transient THz peak field at 100k



Modeling the change of Amplitude of THz field

Expectation



The above/below band gap decay profiles of transient THz peak field at 100k

The above band gap dispersion can be simply described by the combination of two exponential function.

$$Y_1 = 8 \times 10^{-6} + 1 \times 10^{-4} e^{-x/13.3} + 3 \times 10^{-4} e^{-x/124}$$



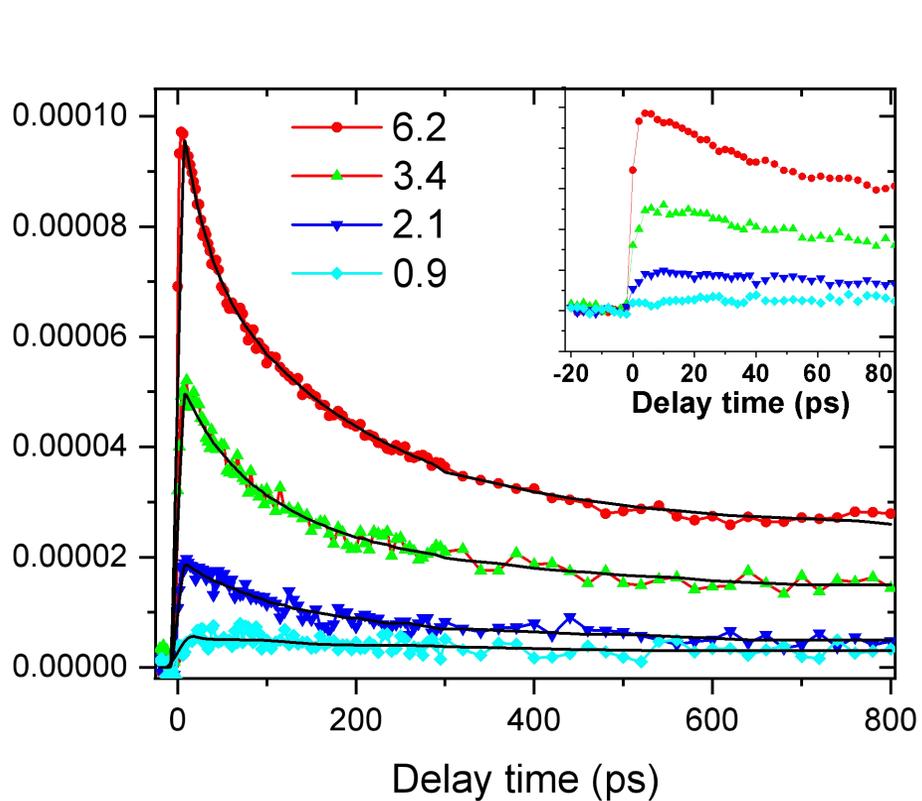
Bulk state and surface state

The below band gap dispersion shows only one exponential dispersion.



Surface state

THz field change

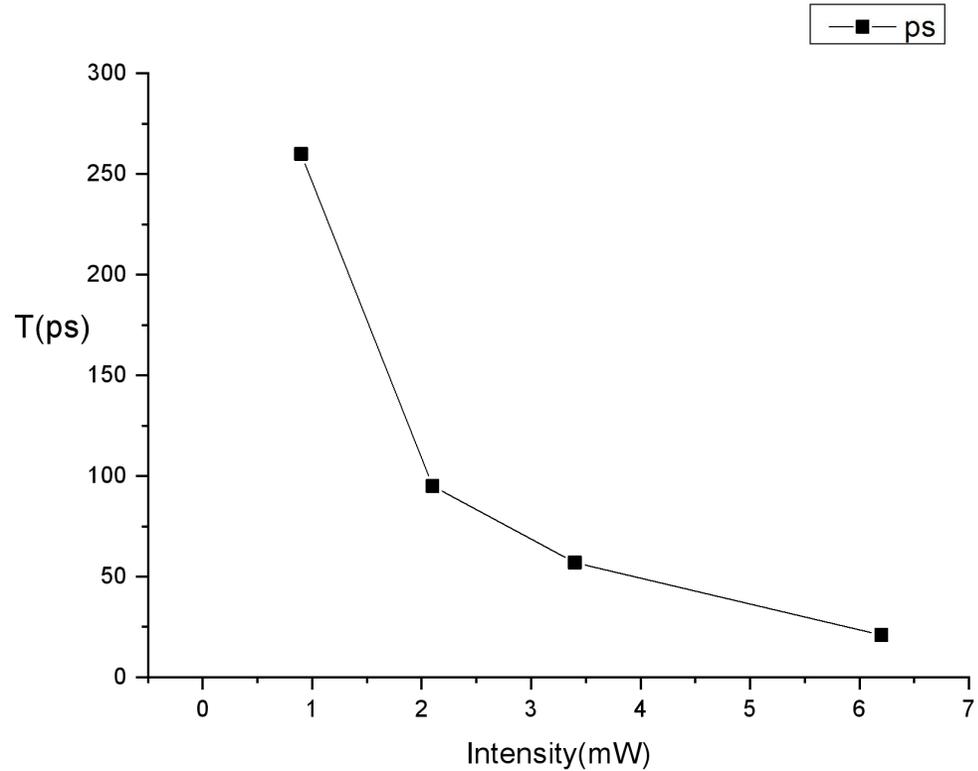


MIR pump ($8\mu\text{m}$)- THz probe THz field change ΔE_{THz}

The THz field change can well fit with two exponential function.



Two decay processes.



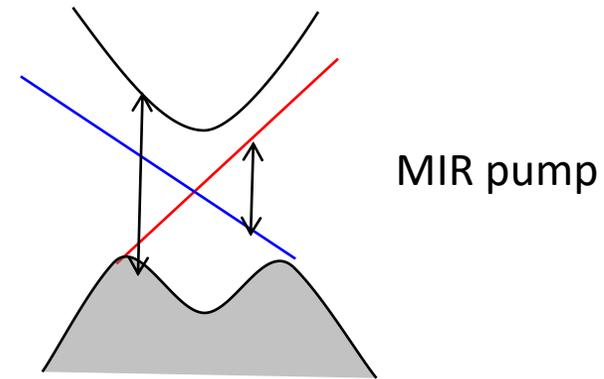
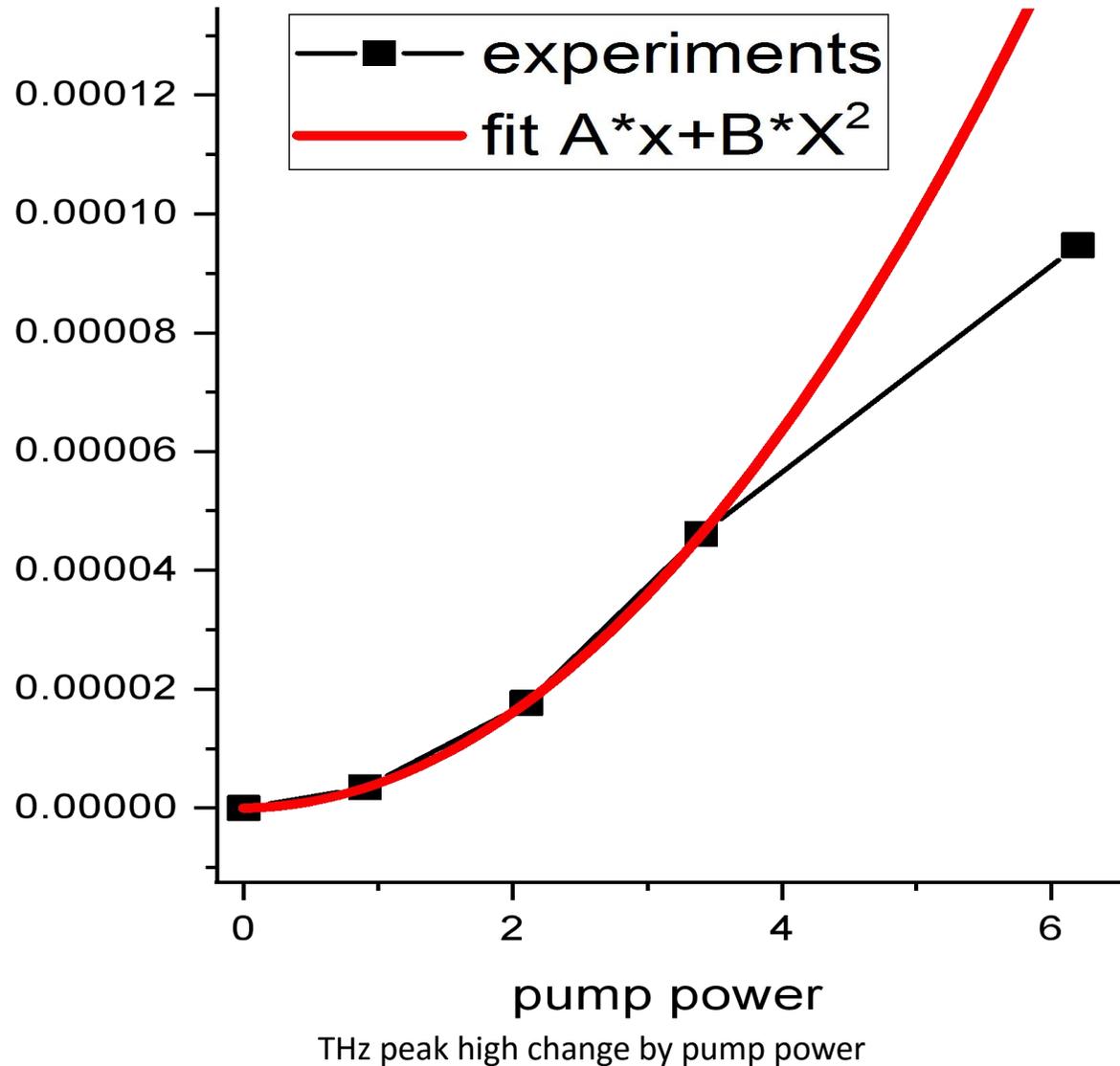
Effective lifetime with different pump intensity

With increasing intensity, the effective life time becomes shorter.



Number of photon effects the the life time.

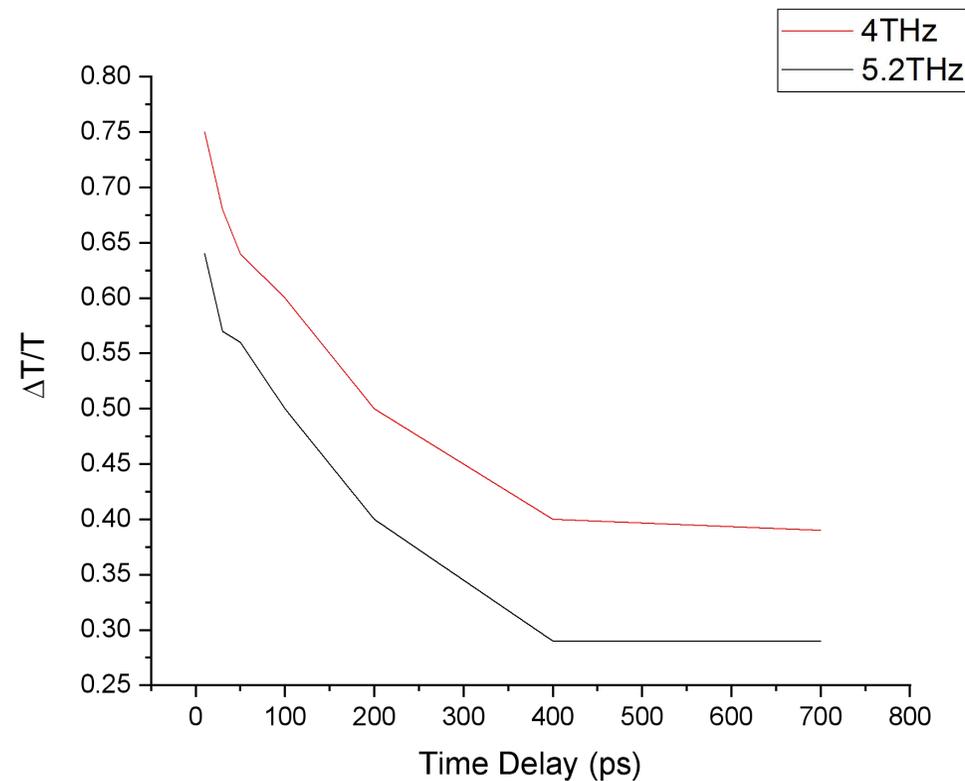
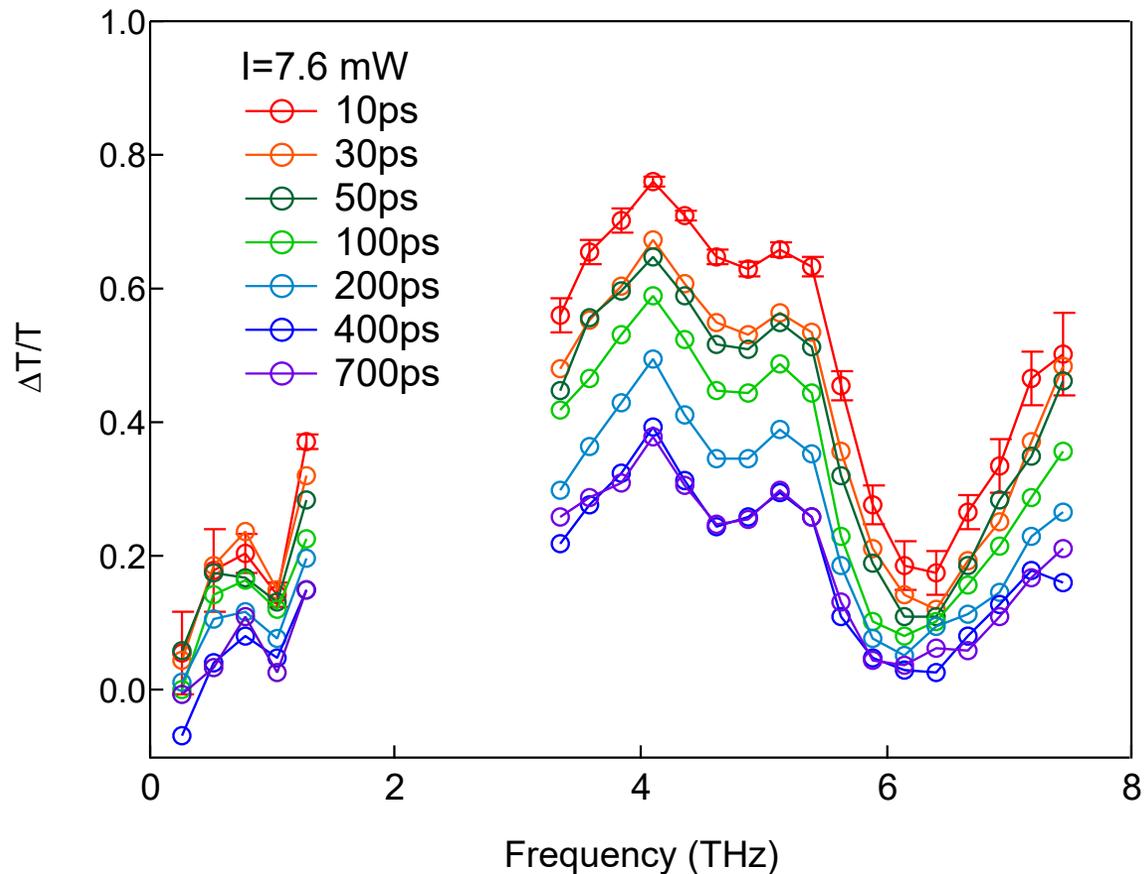
Below gap pump



Below gap pump:

- Bulk to bulk (two photons absorption)
Band gap energies $\approx 0.3\text{eV}$
pump beam energies $\approx 0.15\text{eV}$
- Surface to surface (one photon absorption)

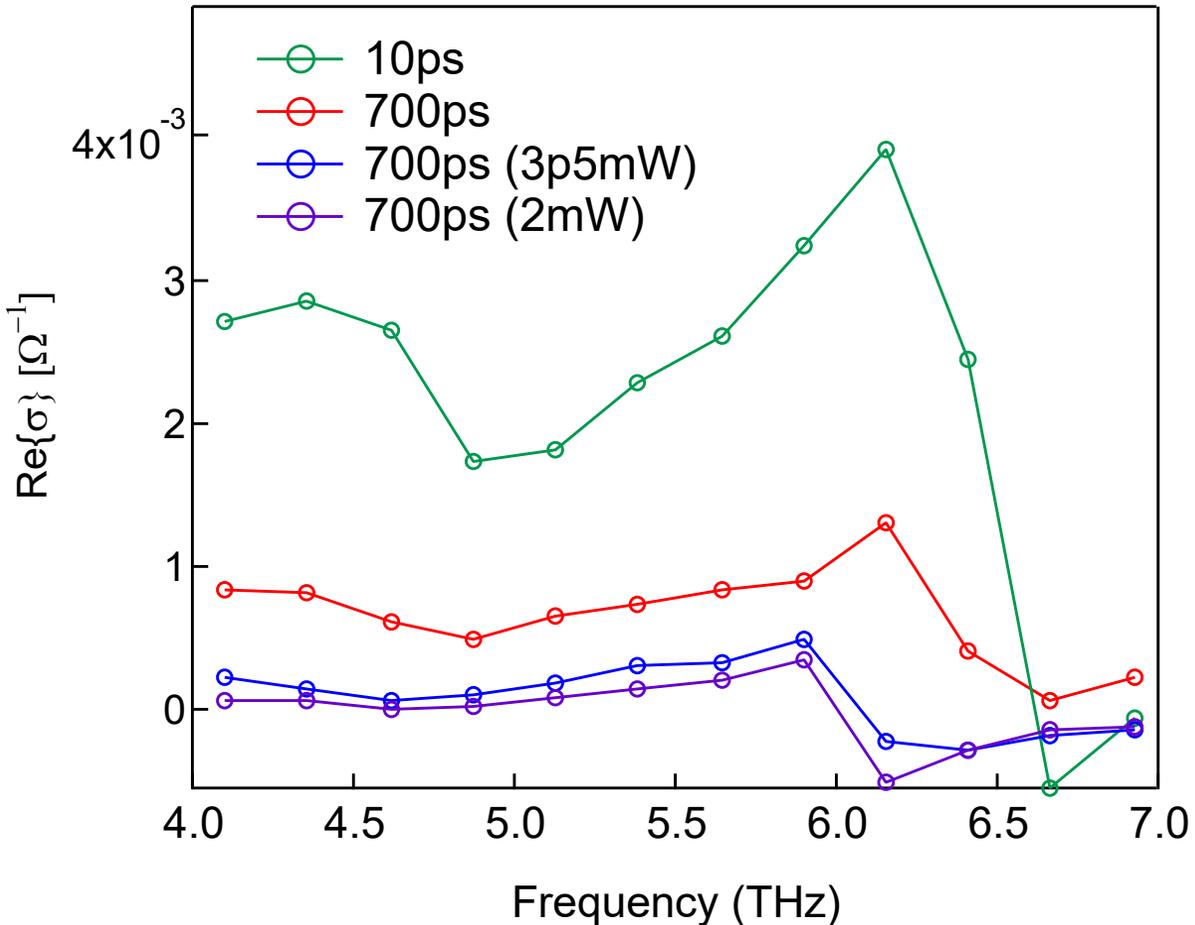
Transmittance change at different delay time



$$(\Delta T / T) = (T_{\tau > 0} - T_{\tau < 0}) / T_{\tau < 0}$$

Transmittance becomes smaller in longer decay time, but we can still see an offset after 700ps.

Photo induced optical conductance



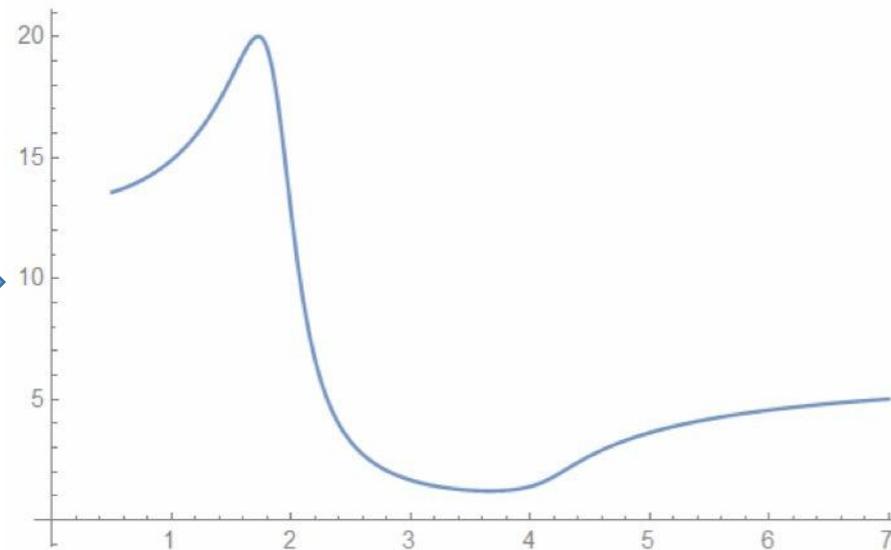
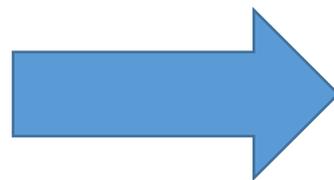
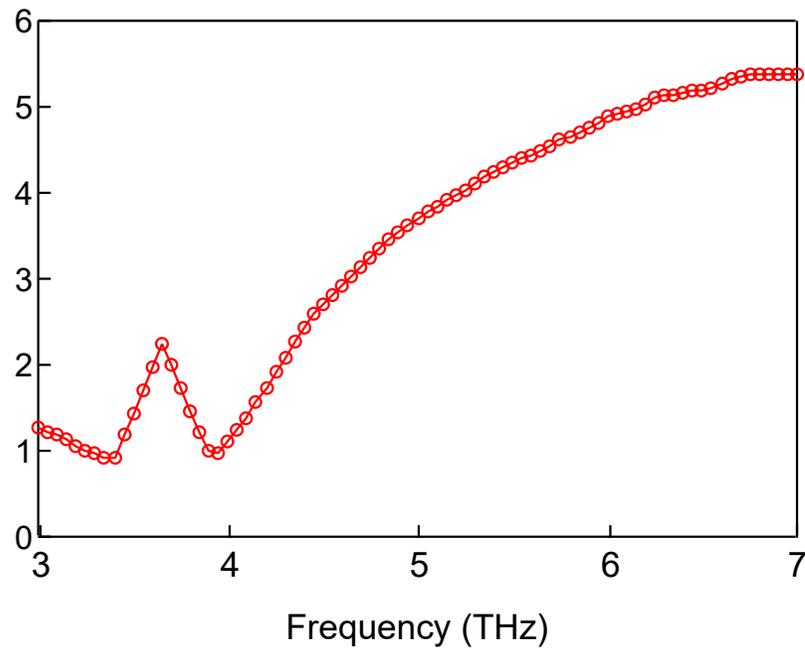
- Photo induced optical conductance

$$\tilde{E}_{exc}(\omega)/\tilde{E}_0(\omega) = (1 + n)/(1 + n + Z_0\Delta G)$$

$\tilde{E}_{exc}(\omega)$ is the complex fourier amplitude of the sample signal.
 $\tilde{E}_0(\omega)$ is the complex fourier amplitude of the reference signal.
 n is the complex refractive index of the sample.
 Z_0 is the impedance of free space.
 ΔG is the transient photoinduced optical conductance.

Refractive index (Exp. & Lorentz model)

Real



Imaginary

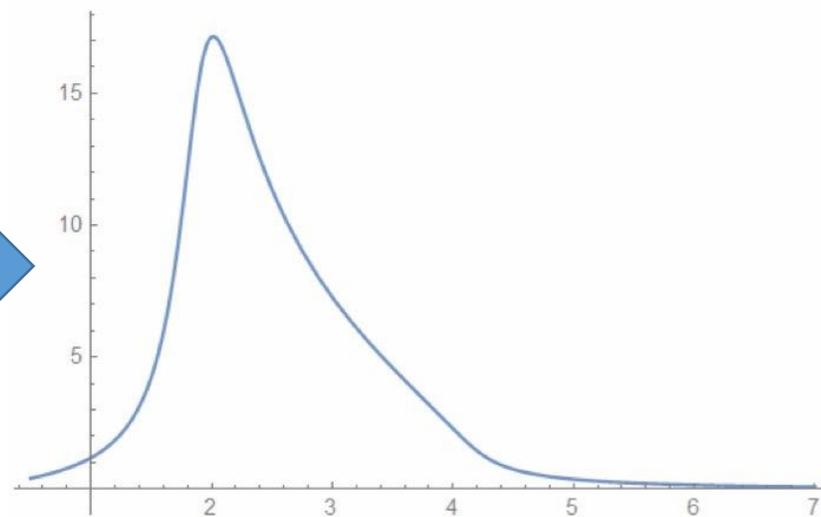
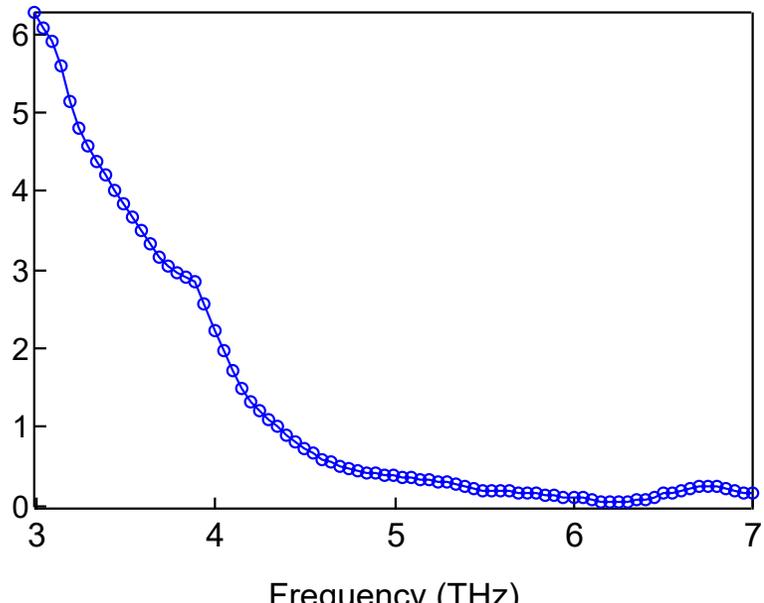
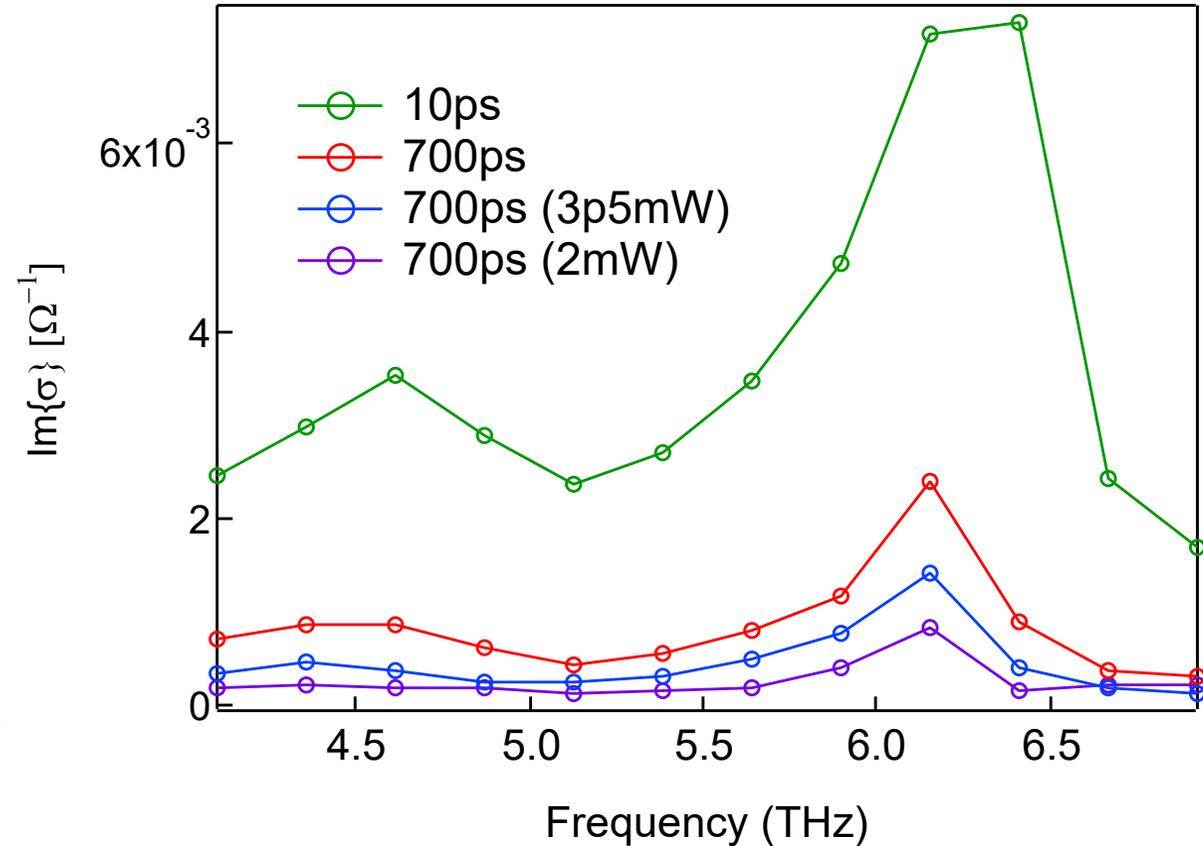
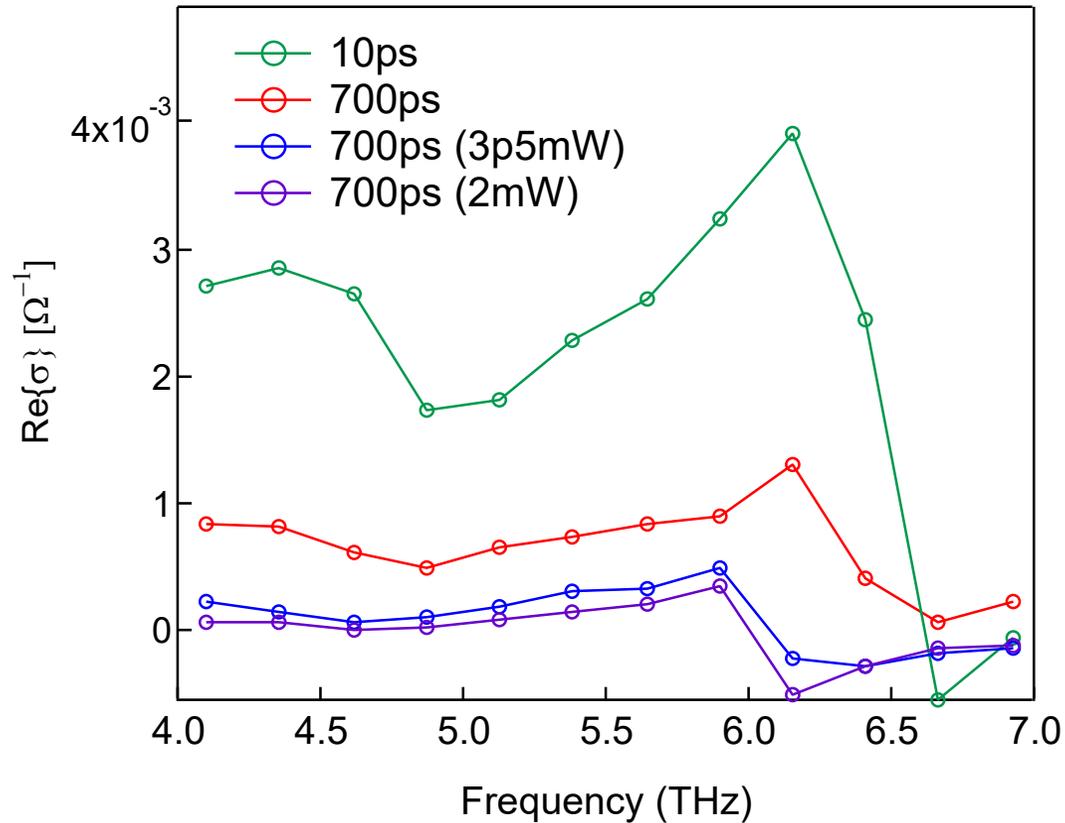


Photo induced optical conductance



The photo-induced conductance fits the Drude model!

However, sample thickness $\sim 6\mu\text{m}$, which is not very accurate!!!

The assumption of internal reflection is also not accurate, which effects the shape of the spectrum!

Summary

- BSTS has a long life time in the surface state.
- Above gap pump perform Bulk to Bulk excitation, below gap pump perform Bulk to Bulk excitation, and surface to surface excitation.
- The photo-induced conductance of BSTS fits the Drude model, and propably the scattering rate and plasma frequency can be extracted.

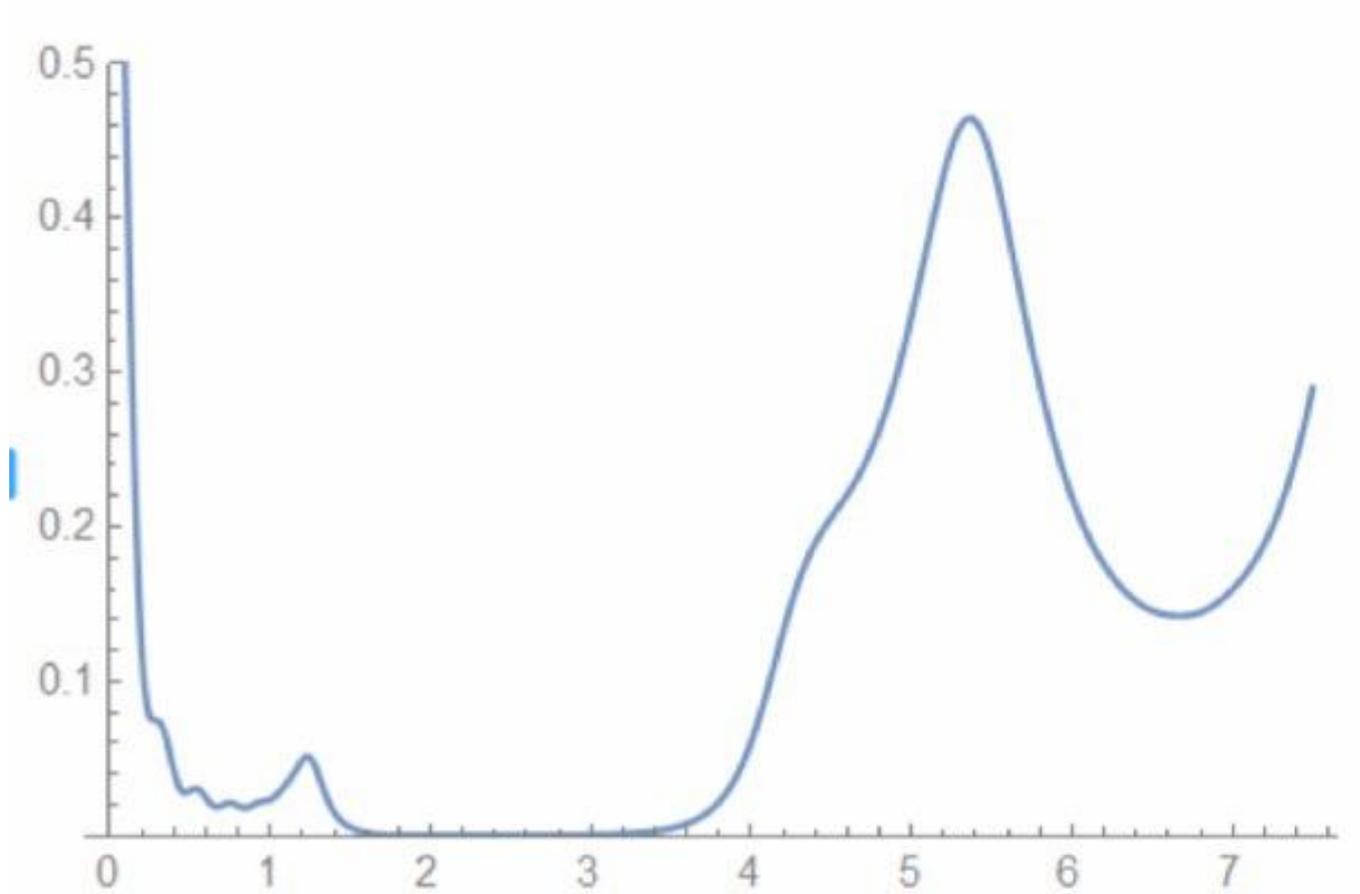
Future plan

- Extract the photo-induce conductance
- Calculate the plasmon frequency and scattering rate



Explain the model better

Transmittance (Lorentz-model)



Calculation $\Delta T/T$

Lorentz-model (bulk)

+ pump induced surface conductivity ($\sigma \sim 0.003$)

